



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ECH8663R — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- 2.5V drive
- Common-drain type
- Protection diode in
- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

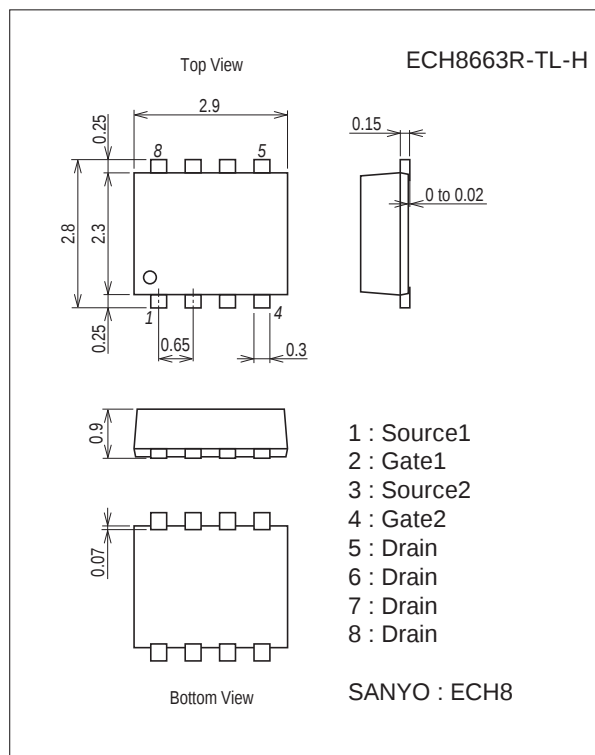
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		8	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.4	W
Total Power Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

unit : mm (typ)

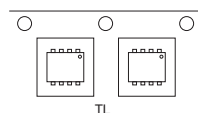
7011A-003



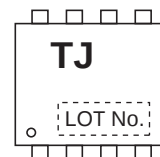
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

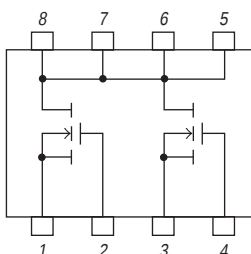
Packing Type : TL



Marking



Electrical Connection

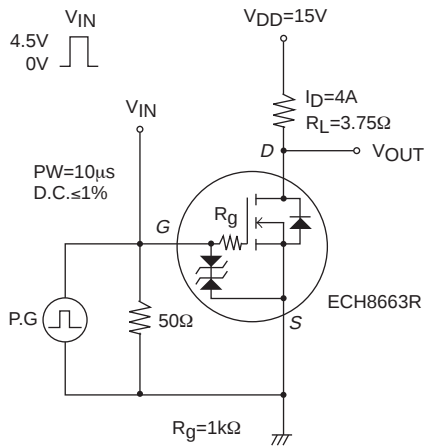


ECH8663R

Electrical Characteristics at Ta=25°C

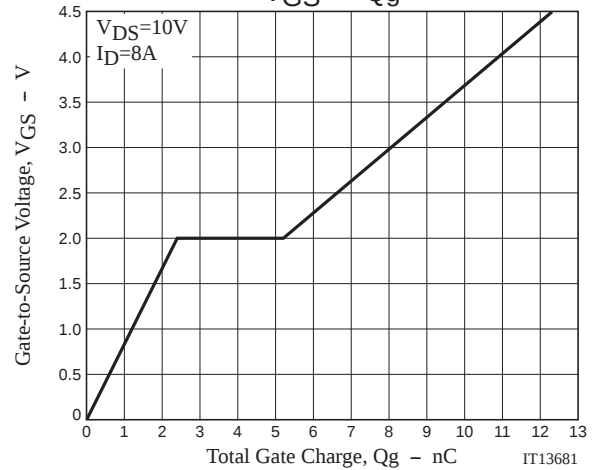
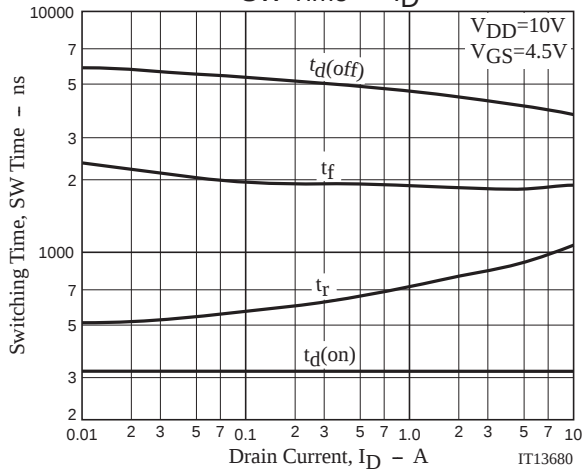
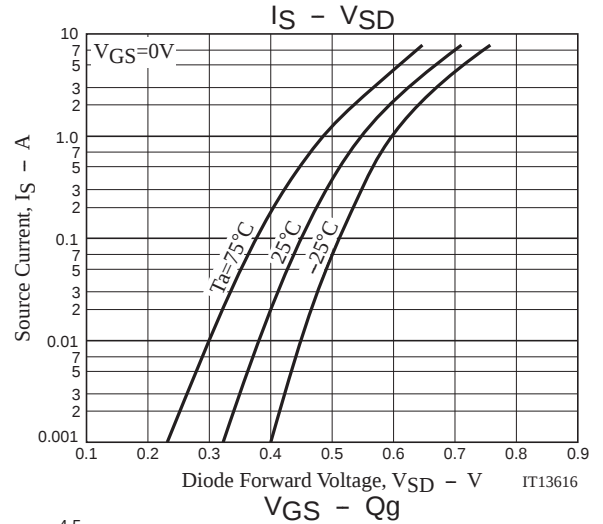
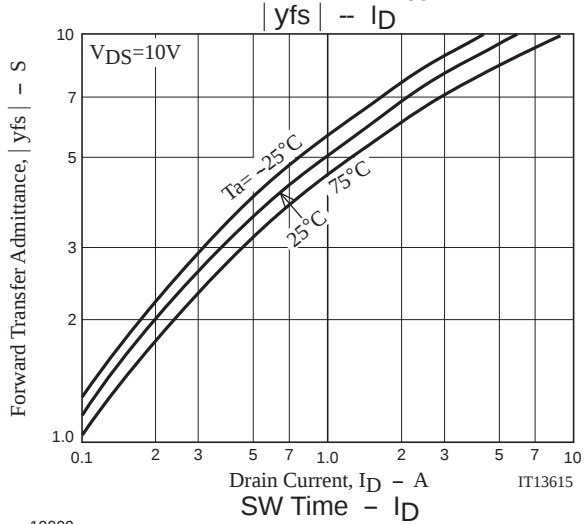
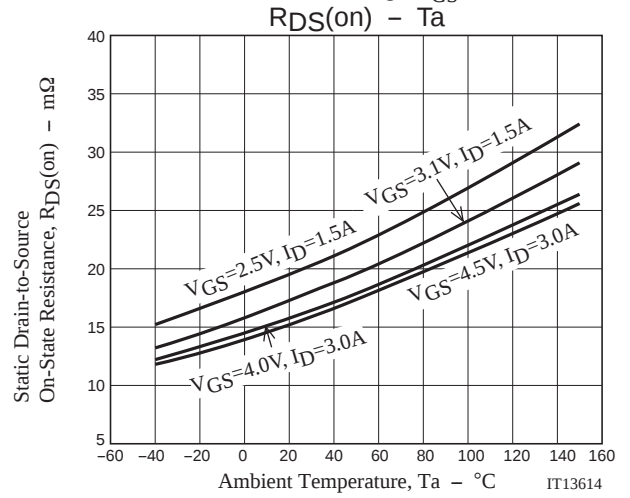
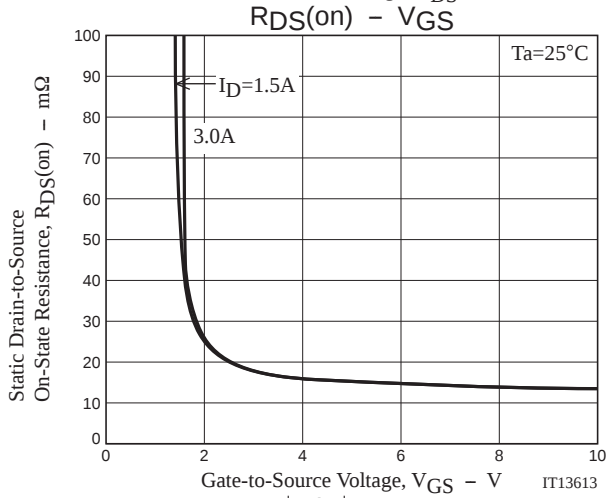
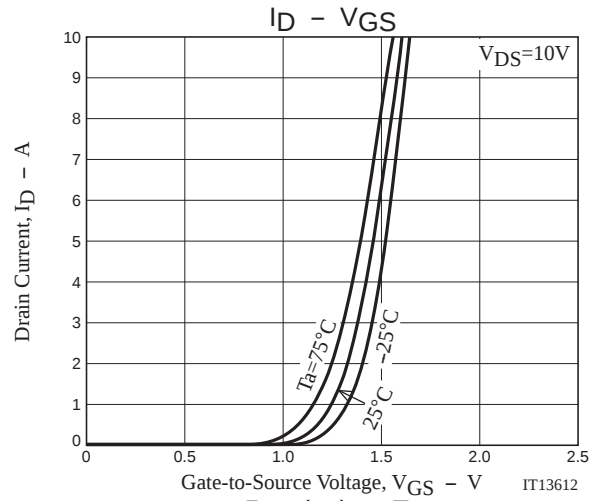
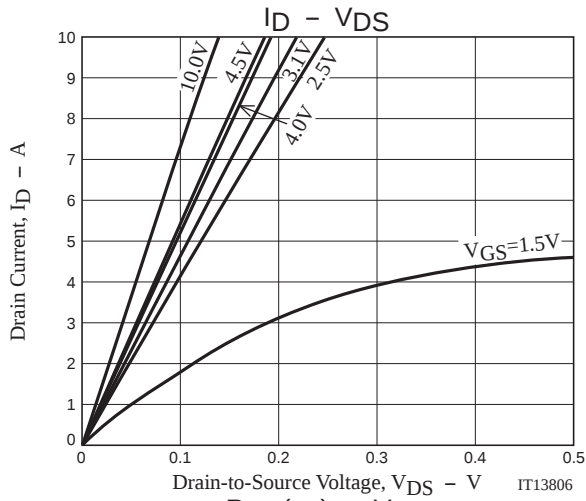
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	0.5		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=4A$	5	8.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=4A, V_{GS}=4.5V$	10.5	15.5	20.5	$m\Omega$
	$R_{DS(on)2}$	$I_D=4A, V_{GS}=4.0V$	11	16	21	$m\Omega$
	$R_{DS(on)3}$	$I_D=2A, V_{GS}=3.1V$	12	17.5	23	$m\Omega$
	$R_{DS(on)4}$	$I_D=2A, V_{GS}=2.5V$	12	20	28	$m\Omega$
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		320		ns
Rise Time	t_r			850		ns
Turn-OFF Delay Time	$t_{d(off)}$			4200		ns
Fall Time	t_f			1800		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=8A$		12.3		nC
Gate-to-Source Charge	Q_{gs}			2.4		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2.8		nC
Diode Forward Voltage	V_{SD}	$I_S=8A, V_{GS}=0V$		0.75	1.2	V

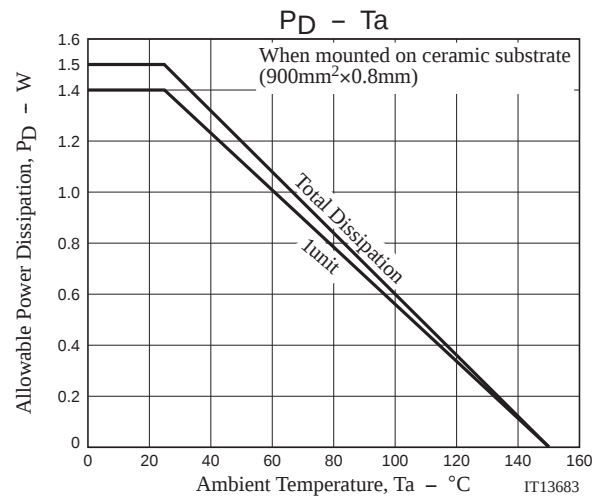
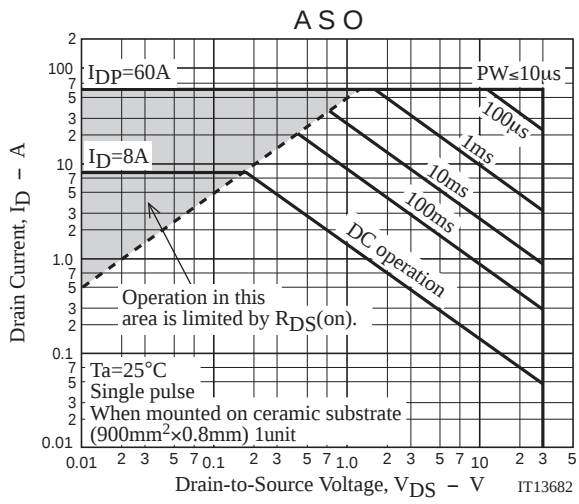
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ECH8663R-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free





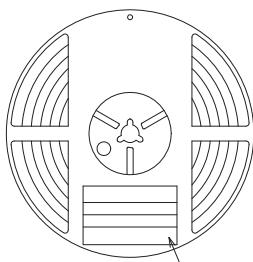
Embossed Taping Specification

ECH8663R-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label

Type No.
LOT No.
Quantity
Origin

Reel label, Inner box label
(unit:mm)

(P) TYPE	000000000
(1) LOT	00
(Q) QTY	0,000 (1) LEAD FREE *
(2) SPECIAL	
	20722005310C
	ASSEMBLY:**** (DIFFUSION:****)

Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

TYPE CODE	00000000000000000000
TYPE	00000000
QTY	0,000 PCS (1) LEAD FREE *
LOT	00000000
PACKAGE	00000000
SPECIAL	
	20722005310C
	ASSEMBLY:**** (DIFFUSION:****)

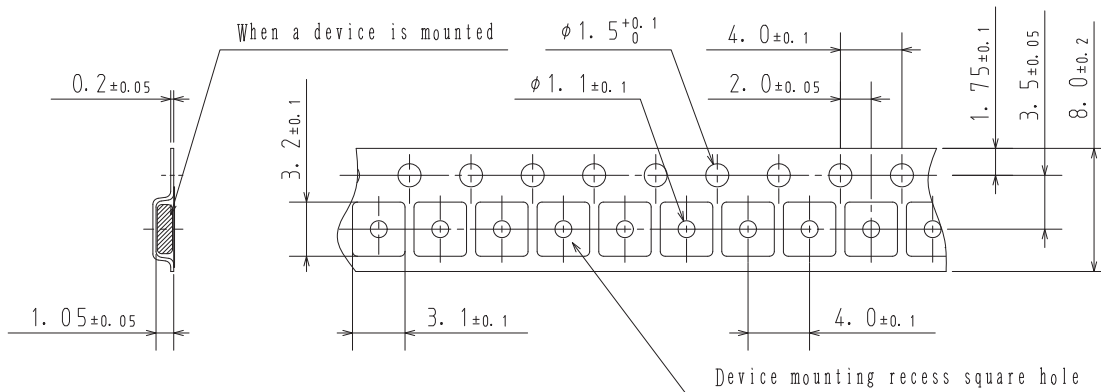
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

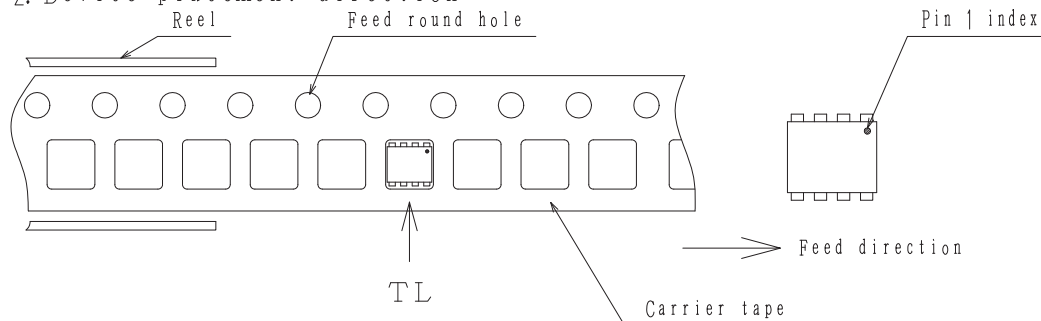
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



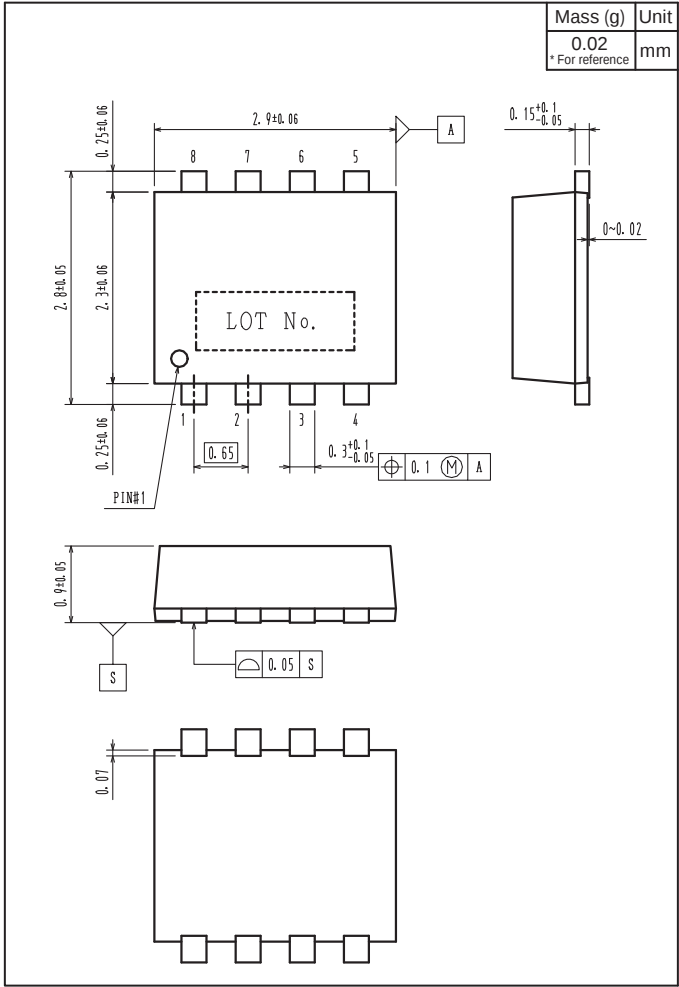
2-2. Device placement direction



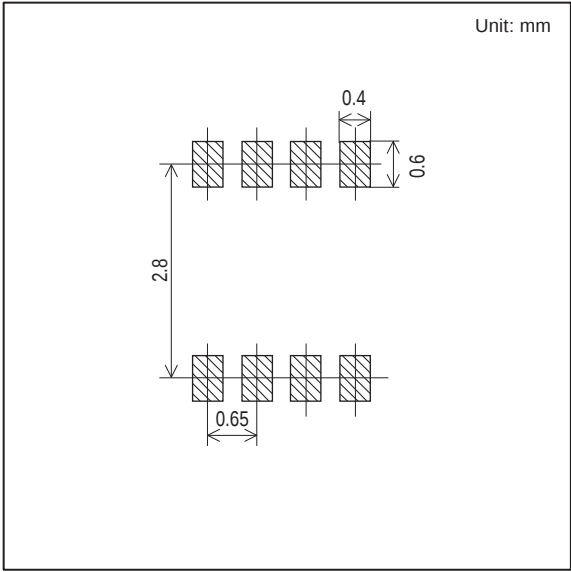
Those with pin 1 index on the feed hole side.....TL

Outline Drawing

ECH8663R-TL-H



Land Pattern Example



Note on usage : Since the ECH8663R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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